

ABSTRACT OF THE DISCLOSURE

It is disclosed a method of forming fine patterns comprising: covering a substrate having photoresist patterns thereon made of a photoresist composition which is sensitive to high energy light rays with wavelength of 200 nm or shorter or electron beam radiation, with an over-coating agent for forming fine patterns, applying heat treatment to cause thermal shrinkage of the over-coating agent so that the spacing between adjacent photoresist patterns is lessened by the resulting thermal shrinking action, and removing the over-coating agent substantially completely. The present invention provides a method of forming fine patterns whereby fine patterns having pattern width or diameter of 100 nm or shorter and being excellent in uniformity (in-plane uniformity), etc. can be formed by ultrafine processing using high energy light rays with wavelength of 200 nm or shorter or electron beams.